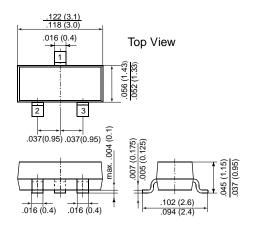
MMBTA06

Small Signal Transistors (NPN)

SOT-23



Dimensions in inches and (millimeters)
Pin configuration
1 = Base, 2 = Emitter, 3 = Collector.

FEATURES

- NPN Silicon Epitaxial Planar Transistor for switching and amplifier applications.
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- As complementary type, the PNP transistor MMBTA56 is recommended.
- ◆ This transistor is also available in the TO-92 case with the type designation MPSA06.

MECHANICAL DATA

Case: SOT-23 Plastic Package **Weight:** approx. 0.008g

Marking code: 1GM

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	VALUE	UNIT
Collector-Base Voltage	Vсво	80	V
Collector-Emitter Voltage	VCEO	80	V
Emitter-Base Voltage	VEBO	4.0	V
Collector Current	Ic	500	mA
Power Dissipation at T _A = 25 °C	Ptot	255 ⁽¹⁾ 300 ⁽²⁾	mW
Thermal Resistance Junction to Ambient Air	R _θ JA	560 ¹⁾	K/W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-65 to +150	°C

¹⁾Device on fiberglass substrate, see layout



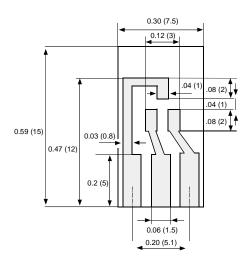
²⁾ Device on alumina subtrate

MMBTA06

ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	.MAX.	UNIT
Collector-Emitter Breakdown Voltage at Ic = 1 mA, IB = 0	V(BR)CEO	80	_	V
Emitter-Base Breakdown Voltage at IE = 100 μ A, IC = 0	V _{(BR)EBO}	4.0	_	V
Collector-Emitter Cutoff Current V _{CE} = 60 V, I _B = 0	Ices	-	100	nA
Collector-Base Cutoff Current VCB = 80 V, IE = 0	Ісво	-	100	nA
Collector Saturation Voltage at I _C = 100 mA, I _B = 10 mA	VCEsat	-	0.25	V
Base-Emitter On Voltage at I _C = 10 mA, I _B = 1 mA	VBE(on)	-	1.2	V
DC Current Gain at V _{CE} = 1 V, I _C = 10 mA at V _{CE} = 1 V, I _C = 100 mA	hFE hFE	100 100	_ _	- -
Gain-Bandwidth Product at Vce = 2 V, Ic = 10 mA, f = 100 MHz	fτ	100	_	MHz



Layout for R_{thJA} test

Thickness: Fiberglass 0.059 in (1.5 mm)
Copper leads 0.012 in (0.3 mm)

